

AMENDMENTS TO THE ABSTRACT:

Delete the current Abstract and replace therewith the attached replacement Abstract of the Disclosure.

ABSTRACT OF THE DISCLOSURE

[[The]] A semiconductor photodetecting device ~~comprises~~ including a PIN photodiode formed on an SI-InP substrate [[10]]; a buried optical waveguide portion [[12a]] formed on the SI-InP substrate [[10]] and including the film thickness continuously increased toward the PIN photodiode [[32]] and an InP clad layer [[20a]] covering the upper surface and the side surface of the InGaAsP core layer [[18]]; and a ridge-shaped connection optical waveguide portion [[12b]] formed on the SI-InP substrate [[10]] between the PIN photodiode [[32]] and the buried optical waveguide portion [[12a]] and including the InGaAsP core layer [[18]] and the InP clad layer [[20a]] selectively covering only the upper surface of the InGaAsP core layer [[18]].